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SEMICONDUCTOR



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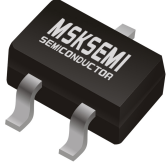
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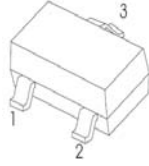
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Product data sheet

FMMT495 TRANSISTOR (NPN)



SOT - 23



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

FEATURE

- Low $V_{CE(sat)}$
- h_{FE} characterised up to 1A for high current gain hold up
- For general amplification

MARKING: 495

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

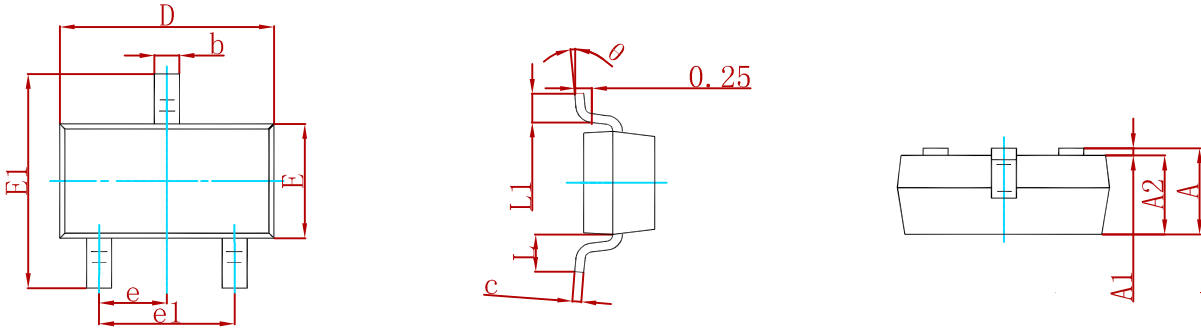
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	170	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	1	A
P_C	Collector Power Dissipation	250	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	500	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	170			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=10\text{mA}, I_B=0$	150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=150\text{V}, I_E=0$			0.1	μA
Collector cut-off current	I_{CES}	$V_{CE}=150\text{V}, V_{BE}=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=10\text{V}, I_C=1\text{mA}$	100			
	$h_{FE(2)}^*$	$V_{CE}=10\text{V}, I_C=250\text{mA}$	100		300	
	$h_{FE(3)}^*$	$V_{CE}=10\text{V}, I_C=500\text{mA}$	50			
	$h_{FE(4)}^*$	$V_{CE}=10\text{V}, I_C=1\text{A}$	10			
Collector-emitter saturation voltage	$V_{CE(sat)(1)}^*$	$I_C=250\text{mA}, I_B=25\text{mA}$			0.2	V
	$V_{CE(sat)(2)}^*$	$I_C=500\text{mA}, I_B=50\text{mA}$			0.3	V
Base-emitter turn-on voltage	$V_{BE(on)}^*$	$V_{CE}=10\text{V}, I_C=500\text{mA}$			1	V
Base-emitter saturation voltage	$V_{BE(sat)}^*$	$I_C=500\text{mA}, I_B=50\text{mA}$			1	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			10	pF

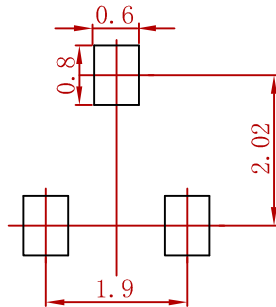
*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2.0\%$.

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
FMMT495	SOT-23	3000

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